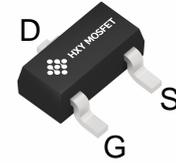


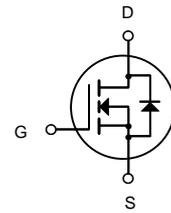


Description

The HDMN24H11DS7 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge and operation with gate voltages as low as 4.5V. This device is suitable for use as a Battery protection or in other Switching application.



SOT-23



N-Channel MOSFET

General Features

$V_{DS} = 240V$ $I_D = 0.1A$

$R_{DS(ON)} < 5\Omega @ V_{GS}=10V$

Application

Battery protection

Load switch

Uninterruptible power supply

Package Marking and Ordering Information

Product ID	Pack	Marking	Qty(PCS)
HDMN24H11DS7	SOT-23	SR	3000

Absolute Maximum Ratings ($T_C=25^\circ C$ unless otherwise noted)

Symbol	Parameter	Limit	Unit	
V_{DS}	Drain-Source Voltage	240	V	
V_{GS}	Gate-Source Voltage	± 20	V	
I_D	Continuous Drain Current ($T_J = 150^\circ C$)	$T_A = 25^\circ C$	0.1	A
		$T_A = 100^\circ C$	0.09	
I_{DM}	Drain Current-Pulsed	0.4	A	
P_D	Maximum Power Dissipation	0.36	W	
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 150	$^\circ C$	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient	200	$^\circ C/W$	



Electrical Characteristics (T_A=25°C unless otherwise noted)

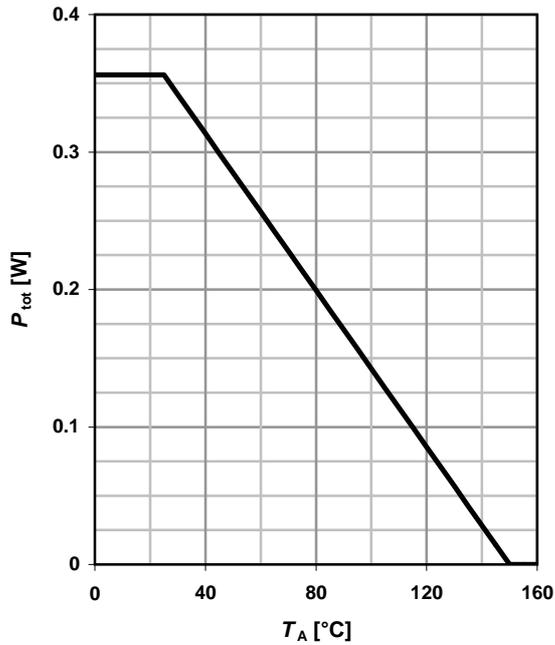
Parameter	Symbol	Conditions	Values			Unit
			min.	typ.	max.	
Thermal resistance, junction - minimal footprint	R _{thJA}		-	-	350	K/W
Drain-source breakdown voltage	V _{(BR)DSS}	V _{GS} =0 V, I _D =250 μA	240	-	-	V
Gate threshold voltage	V _{GS(th)}	V _{DS} =0 V, I _D =56 μA	0.8	1.4	1.8	
Drain-source leakage current	I _{D(off)}	V _{DS} =240 V, V _{GS} =0 V, T _j =25 °C	-	-	0.01	μA
		V _{DS} =240 V, V _{GS} =0 V, T _j =150 °C	-	-	5	
Gate-source leakage current	I _{GSS}	V _{GS} =20 V, V _{DS} =0 V	-	-	10	nA
Drain-source on-state resistance	R _{DS(on)}	V _{GS} =4.5 V, I _D =0.09 A	-	6	10	Ω
		V _{GS} =10 V, I _D =0.1 A	-	3	5	
Transconductance	g _{fs}	V _{DS} >2 I _D R _{DS(on)max} , I _D =0.08 A	0.06	0.13	-	S
Input capacitance	C _{iss}	V _{GS} =0 V, V _{DS} =25 V, f=1 MHz	-	58	77	pF
Output capacitance	C _{oss}		-	7.3	10	
Reverse transfer capacitance	C _{rss}		-	2.8	4.2	
Turn-on delay time	t _{d(on)}	V _{DD} =120 V, V _{GS} =10 V, I _D =0.1 A, R _G =6 Ω	-	3.3	5.0	ns
Rise time	t _r		-	3.1	4.6	
Turn-off delay time	t _{d(off)}		-	13.7	20	
Fall time	t _f		-	64.5	97	
Gate to source charge	Q _{gs}	V _{DD} =192 V, I _D =0.1 A, V _{GS} =0 to 10 V	-	0.16	0.22	nC
Gate to drain charge	Q _{gd}		-	0.8	1.2	
Gate charge total	Q _g		-	2.1	3.1	
Gate plateau voltage	V _{plateau}		-	2.90	-	V
Diode continuous forward current	I _S	T _A =25 °C	-	-	0.11	A
Diode pulse current	I _{S,pulse}		-	-	0.43	
Diode forward voltage	V _{SD}	V _{GS} =0 V, I _F =0.1 A, T _j =25 °C	-	0.81	1.2	V
Reverse recovery time	t _{rr}	V _R =120 V, I _F =0.1 A, di _F /dt=100 A/μs	-	42.9	64.3	ns
Reverse recovery charge	Q _{rr}		-	22.6	34	nC



Typical Characteristics

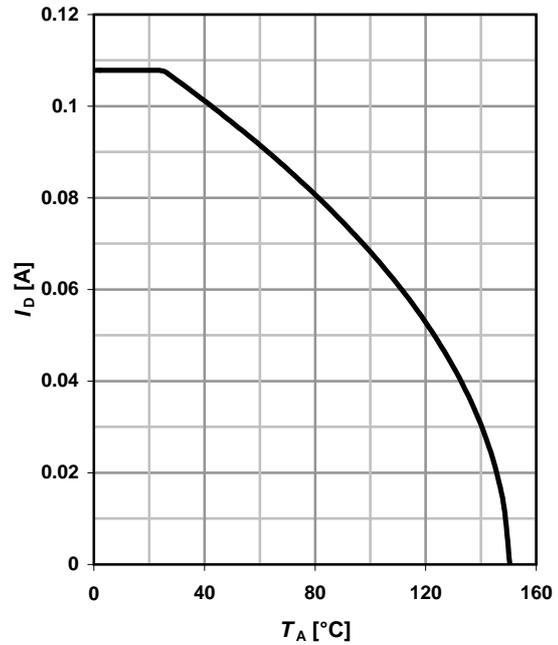
1 Power dissipation

$$P_{\text{tot}}=f(T_A)$$



2 Drain current

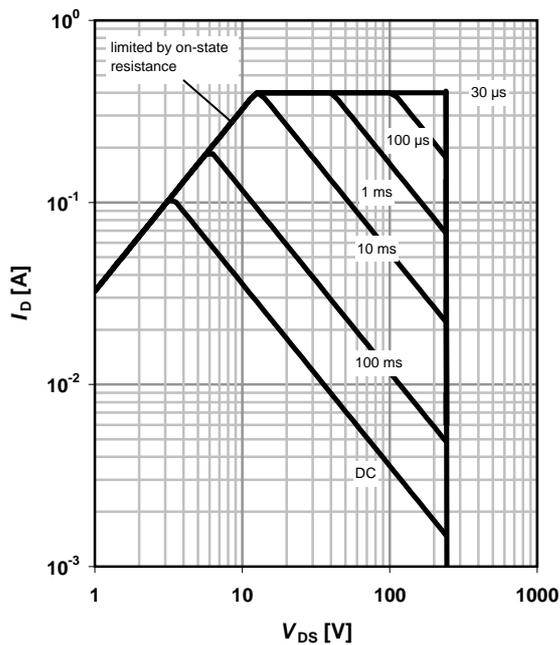
$$I_D=f(T_A); V_{\text{GS}}\geq 10\text{ V}$$



3 Safe operating area

$$I_D=f(V_{\text{DS}}); T_A=25\text{ °C}; D=0$$

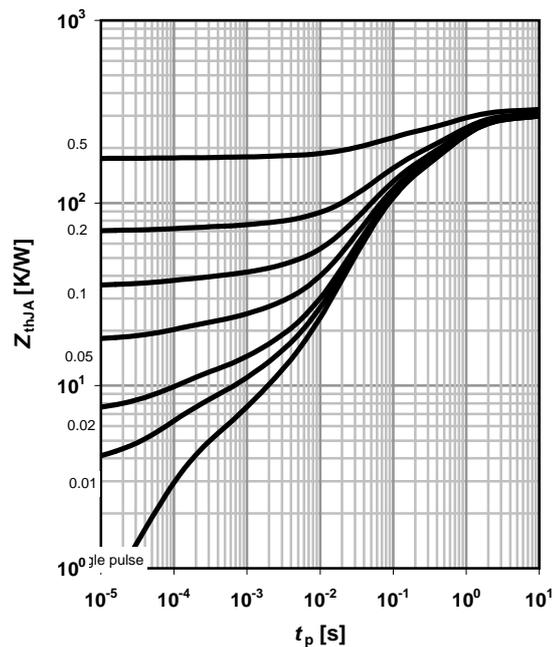
parameter: t_p



4 Max. transient thermal impedance

$$Z_{\text{thJA}}=f(t_p)$$

parameter: $D=t_p/T$

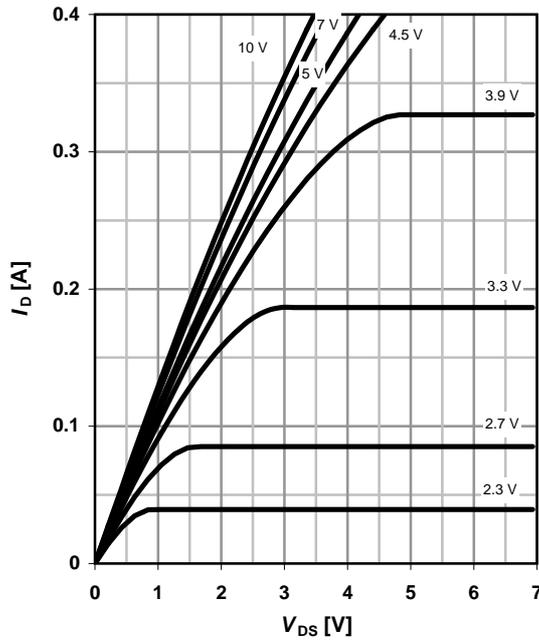




5 Typ. output characteristics

$$I_D = f(V_{DS}); T_j = 25^\circ\text{C}$$

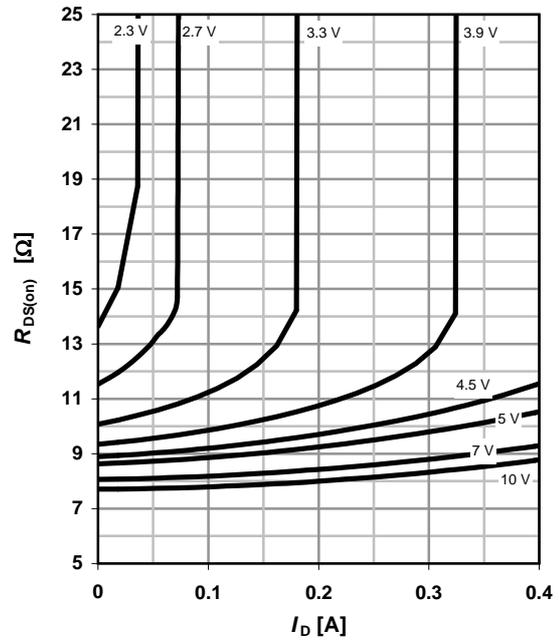
parameter: V_{GS}



6 Typ. drain-source on resistance

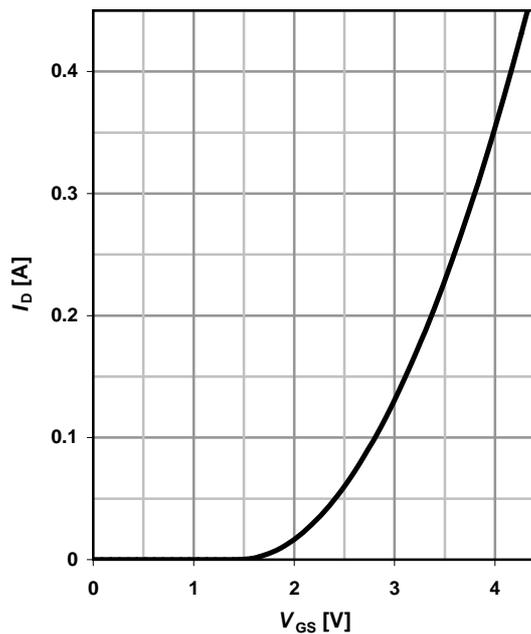
$$R_{DS(on)} = f(I_D); T_j = 25^\circ\text{C}$$

parameter: V_{GS}



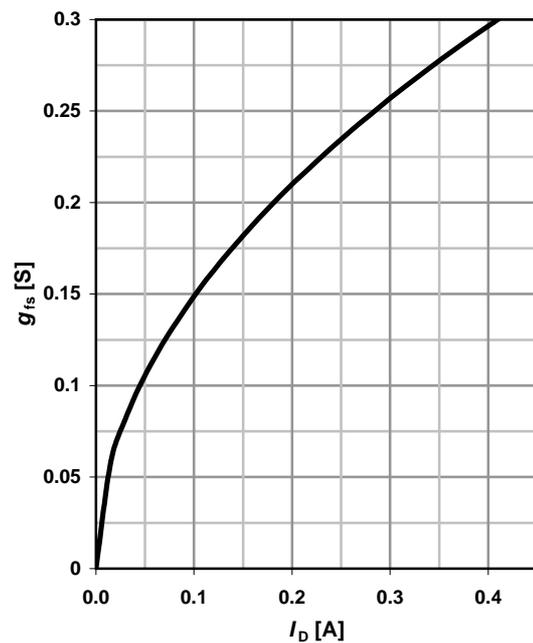
7 Typ. transfer characteristics

$$I_D = f(V_{GS}); |V_{DS}| > 2|I_D|R_{DS(on)max}$$



8 Typ. forward transconductance

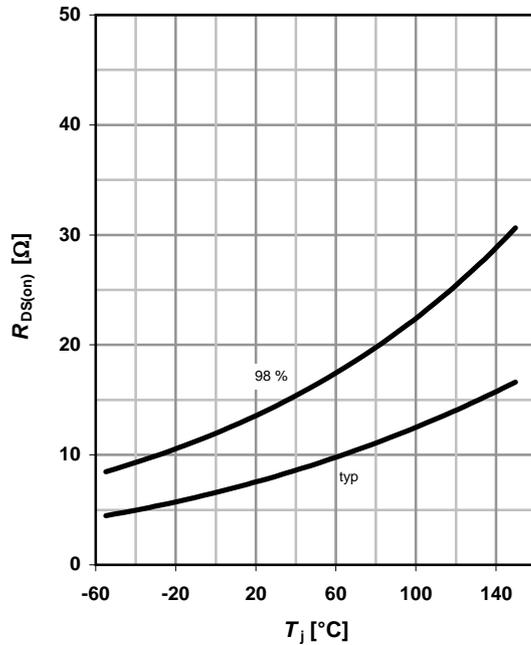
$$g_{fs} = f(I_D); T_j = 25^\circ\text{C}$$





9 Drain-source on-state resistance

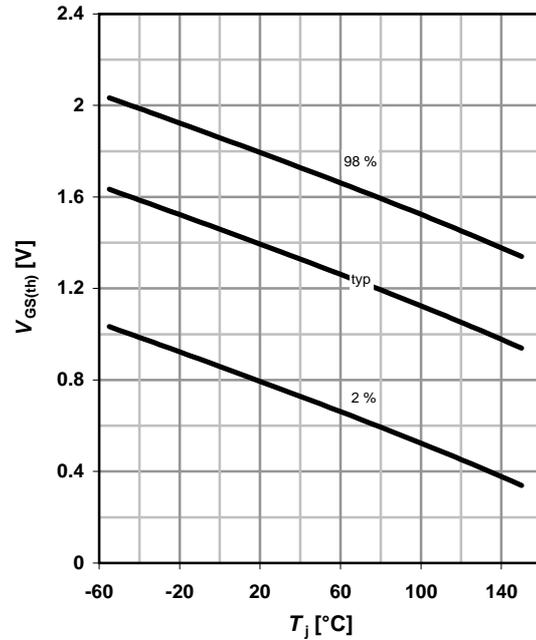
$$R_{DS(on)} = f(T_j); I_D = 0.1 \text{ A}; V_{GS} = 10 \text{ V}$$



10 Typ. gate threshold voltage

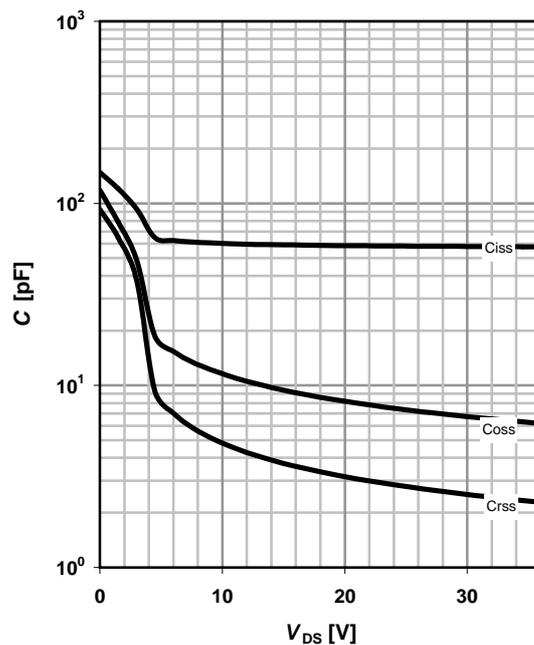
$$V_{GS(th)} = f(T_j); V_{DS} = V_{GS}; I_D = 56 \mu\text{A}$$

parameter: I_D



11 Typ. capacitances

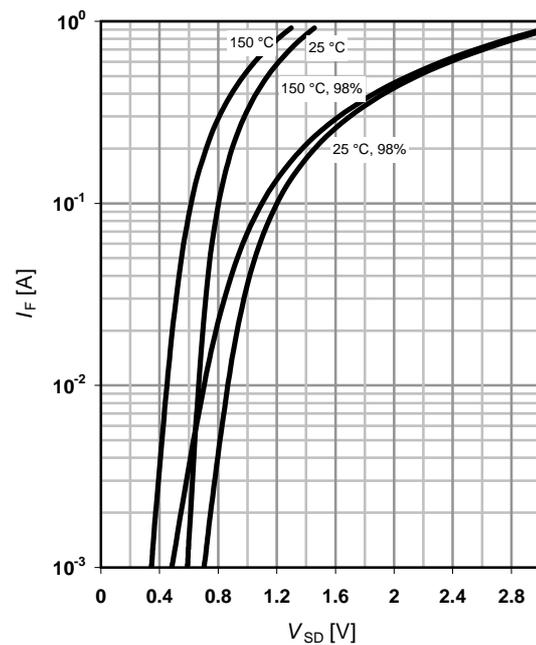
$$C = f(V_{DS}); V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}; T_j = 25^\circ\text{C}$$



12 Forward characteristics of reverse diode

$$I_F = f(V_{SD})$$

parameter: T_j

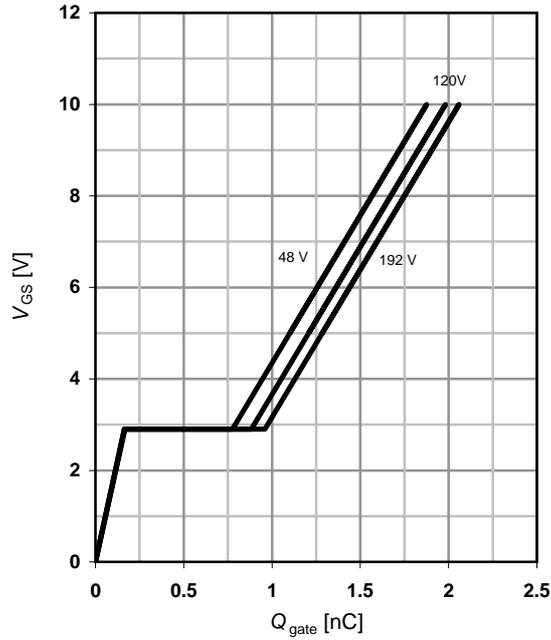




13 Typ. gate charge

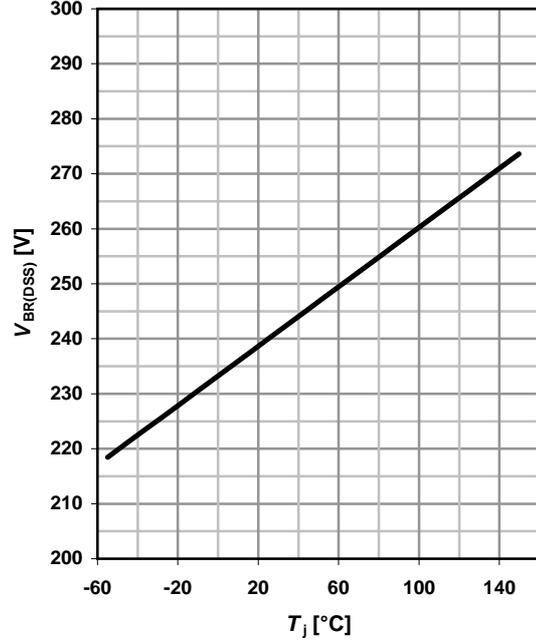
$V_{GS}=f(Q_{gate}); I_D=0.1\text{ A pulsed}$

parameter: V_{DD}



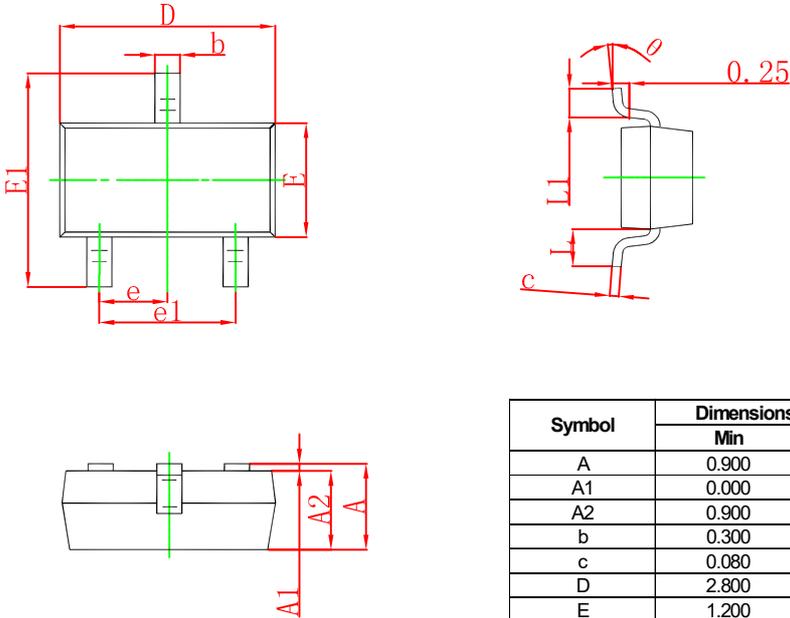
14 Drain-source breakdown voltage

$V_{BR(DSS)}=f(T_j); I_D=250\text{ }\mu\text{A}$



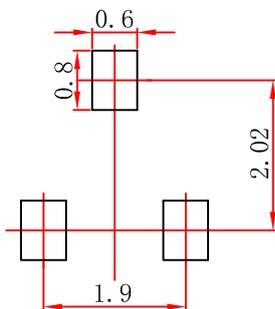


SOT-23 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP		0.037 TYP	
e1	1.800	2.000	0.071	0.079
L	0.550 REF		0.022 REF	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°

SOT-23 Suggested Pad Layout



- Note:
1. Controlling dimension: in millimeters.
 2. General tolerance: $\pm 0.05\text{mm}$.
 3. The pad layout is for reference purposes only.



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